

Sub D1 Cancel
C1 Cancel

irradiating an intense light to said insulating film in an atmosphere comprising an oxygen gas under a pressure of 10 Torr or less.

Sub D2
C2

6. (Twice Amended) A method for manufacturing a semiconductor device comprising the steps of:

forming a semiconductor film comprising amorphous silicon over a substrate;
crystallizing said semiconductor film by irradiating a laser light;
forming an insulating film comprising silicon oxide on the crystallized semiconductor film by a vapor phase deposition; and
irradiating an intense light to said insulating film in an atmosphere comprising an oxygen gas under a pressure of 10 Torr or less.

Sub D3
C3

11. (Twice Amended) A method for manufacturing a semiconductor device comprising the steps of:

forming a semiconductor film comprising amorphous silicon over a substrate;
crystallizing said semiconductor film by irradiating a laser light;
forming an insulating film comprising silicon oxide on the crystallized semiconductor film by a vapor phase deposition using TEOS; and
irradiating an intense light to said insulating film in an atmosphere comprising an oxygen gas under a pressure of 10 Torr or less.

Sub D4
C4

30. (Amended) A method for manufacturing a semiconductor device comprising the steps of:

forming a crystalline semiconductor film over a substrate;
forming an insulating film comprising silicon oxide on said crystalline semiconductor film by a vapor phase deposition; and